IN THE CLAIMS:

The following is a complete listing of the claims in this application, reflects all changes currently being made to the claims, and replaces all earlier versions and all earlier listings of the claims:

1.-24. (Canceled)

25. (Original) A method for manufacturing a semiconductor film comprising the steps of:

preparing a first member including a semiconductor substrate, a semiconductor layer whose resistivity is higher than a resistivity of the semiconductor substrate, and a separation layer provided between the semiconductor substrate and the semiconductor layer; and

separating the semiconductor layer from the semiconductor substrate at the separation layer by heating the first member by induction heating.

26. (Original) A method according to Claim 25, further comprising a step of bonding or attracting a second member which is hardly heated by induction heating, onto the semiconductor layer of the first member, before heating the first member by induction heating.

27. (Original) A method according to Claim 25, further comprising a step of bonding or attracting a second member whose resistivity is higher than a resistivity

of the first member, onto the semiconductor layer of the first member, before heating the first member by induction heating.

28. (Original) A method according to Claim 25, wherein the resistivity of the semiconductor layer is at least 10 times the resistivity of the semiconductor substrate.

29. (Original) A method according to Claim 25, wherein the resistivity of the semiconductor layer is at least 1 Ω •cm, and the resistivity of the semiconductor substrate is equal to or less than 0.1 Ω •cm.

30.-32. (Canceled)

33. (Original) A method according to Claim 25, wherein said step of heating the semiconductor substrate by induction heating comprises a step of mounting the first member on an induction-heating mount around which a coil is wound, and causing a current to flow in the semiconductor substrate by supplying the coil with a high-frequency current.

34. (Original) A method according to Claim 25, further comprising a step of forming slits in the separation layer before heating the first member by induction heating.

35. (Original) A method according to Claim 25, wherein, in said step of heating the first member by induction heating, a tensile force, a compressive force or a shearing force is simultaneously applied to the separation layer.

36. (Original) A method according to Claim 25, wherein, in said step of heating the first member by induction heating, a pressure or a hydrostatic pressure by a fluid is simultaneously applied to the separation layer.

37. (Original) A method according to Claim 25, further comprising a step of removing a residue of the separation layer remaining on the semiconductor layer according to etching, after separating the semiconductor layer.

38. (Original) A method according to Claim 25, further comprising a step of reutilizing a remaining semiconductor substrate for preparing another first member, after separating the semiconductor layer.

39. (Original) A method according to Claim 38, further comprising a step of removing a residue of the separation layer remaining on the semiconductor substrate according to etching, before reutilizing the semiconductor substrate.

40.-58. (Canceled)

59. (New) A method for manufacturing a semiconductor film according to Claim 26, further comprising a step of separating the second member from the semiconductor layer.